

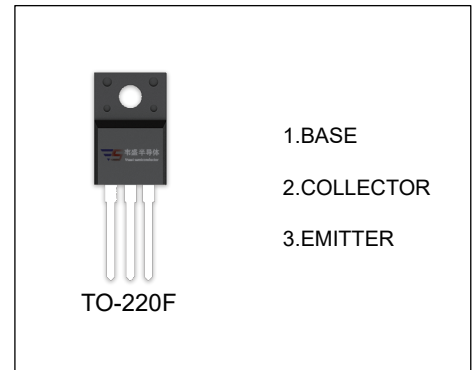
2SB1370 TRANSISTOR (PNP)

FEATURES

- Breakdown Voltage High
- Reverse Cut-off Current Small
- Saturation Voltage Low
- Collector Power dissipation

$$P_{CM} : 2 \text{ W (Tamb=25.)}$$

$$30 \text{ W (Tcase=25.)}$$



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-3	A
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-60V, I _E =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-10	μA
DC current gain	h _{FE} *	V _{CE} =-5V, I _C =-500mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-2A, I _B =-0.2A			-1.5	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-2A, I _B =-0.2A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-500mA, f=5MHz		15		MHz
Out capacitance	Cob	V _{CB} = -10 V, f=1MHz		80		pF

*Pulse test: t_p≤300μS, δ≤0.02.

CLASSIFICATION OF h_{FE}

Rank	E	F
Range	100-200	160-320